WHAT IS CLAIMED IS:

1. A method of manufacturing a flash memory device, comprising the steps of:

performing an ion implantation for controlling a threshold voltage on a semiconductor substrate;

performing a spike annealing for controlling a doping concentration and a doping profile of an implanted dopant;

forming a device isolation film for isolating an active area and a field area on the semiconductor substrate;

forming a gate electrode in which a tunnel oxide film, a floating gate electrode, a dielectric film, and a control gate electrode are deposited on the active area; and

performing an ion implantation for forming junctions on the semiconductor substrate in both sides of the gate electrode to form a DDD junction structure.

2. The method of manufacturing a flash memory device according to claim 1, wherein the ion implantation for controlling a threshold voltage is performed by using a p-type dopant with an ion implantation energy of 5 KeV to 50 KeV and a dose of 1E11 ion/cm^2 to 1E13 ion/㎠.

3. The method of manufacturing a flash memory device according to claim 2, wherein BF_2 is used as the p-type dopant.

4. The method of manufacturing a flash memory device according to claim 1, wherein the spike annealing is performed under NH_3, H_2, or N_2 atmosphere at a temperature in the range of 900℃ to 1,100℃ with a heating rate of 100℃/sec to 250℃/sec.